Fall-2021 UM-SJTU JI Ve311 Lab #2

Instructor: Dr. Chang-Ching Tu

Due: 11:59 am, November 05, 2021 (Friday)

Note:

results.

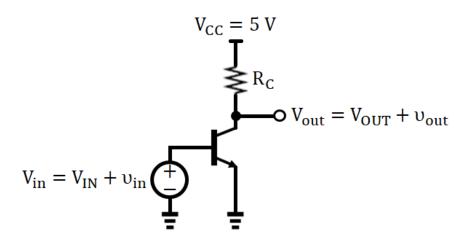
(1) Please use A4 size papers.

(2) The lab report should be submitted online individually.

(3) Use Proteus 8.10 for simulation before the lab session. In the Proteus library, you should be able to find all the components used in the schematics. The lab report must include both the simulation and measurement

1. [Common-Emitter Amplifier]

- (a) [40%] Design and build a common-emitter amplifier in Proteus and on the breadboard which has a voltage gain $A_{\upsilon} > 10$, using **npn BJT 2N3904**. Plot V_{OUT} vs V_{IN} . (Hint: First choose an appropriate R_C . Second, perform DC sweep to find out a V_{IN} at which the magnitude of slope is more than 10. At the same time, make sure the BJT is in the forward-active region. If not working, change for another R_C and repeat the DC sweep analysis again.)
- (b) [30%] For $V_{in} = V_{IN} + 0.01 sin(2\pi 10^2 \cdot time)$, plot $V_{out} = V_{OUT} + \upsilon_{out}$ vs time. Confirm that the amplitude of υ_{out} is equal to $0.01 \times A_{\upsilon}$.
- (c) [30%] For $V_{in} = V_{IN} + 0.01 sin(2\pi 10^7 \cdot time)$, plot $V_{out} = V_{OUT} + \upsilon_{out}$ vs time. Is the amplitude of υ_{out} still equal to $0.01 \times A_{\upsilon}$? If not, explain the possible reasons.



General Purpose Transistors

NPN Silicon

Features

• Pb-Free Packages are Available*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V _{CEO}	40	Vdc
Collector - Base Voltage	V _{CBO}	60	Vdc
Emitter - Base Voltage	V _{EBO}	6.0	Vdc
Collector Current - Continuous	Ic	200	mAdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	P _D	625 5.0	mW mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	1.5 12	W mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS (Note 1)

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	83.3	°C/W

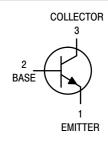
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

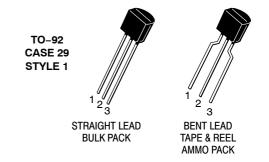
1. Indicates Data in addition to JEDEC Requirements.



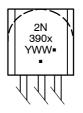
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MARKING DIAGRAMS



x = 3 or 4

Y = Year

WW = Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

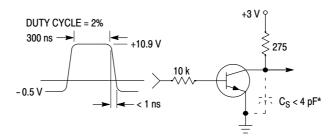
	Characteristic	Symbol	Min	Max	Unit	
OFF CHARACTER	RISTICS				•	•
Collector - Emitter	Breakdown Voltage (Note 2) ($I_C = 1.0 \text{ mAdc}, I_B = 0$))	V _{(BR)CEO}	40	-	Vdc
Collector - Base Br	reakdown Voltage (I _C = 10 μAdc, I _E = 0)	V _{(BR)CBO}	60	-	Vdc	
Emitter-Base Brea	akdown Voltage (I _E = 10 μAdc, I _C = 0)		V _{(BR)EBO}	6.0	-	Vdc
Base Cutoff Currer	nt (V _{CE} = 30 Vdc, V _{EB} = 3.0 Vdc)		I _{BL}	_	50	nAdc
Collector Cutoff Cu	urrent (V _{CE} = 30 Vdc, V _{EB} = 3.0 Vdc)	I _{CEX}	-	50	nAdc	
ON CHARACTERI	ISTICS			1	<u>'</u>	
DC Current Gain (I _C = 0.1 mAdc, V _C	2N3903	h _{FE}	20	_	-	
$(I_C = 1.0 \text{ mAdc}, V_C)$	_{DE} = 1.0 Vdc)	2N3904 2N3903 2N3904		40 35 70	- - -	
$(I_C = 10 \text{ mAdc}, V_C)$	_E = 1.0 Vdc)	2N3903		50	150	
(I _C = 50 mAdc, V _C	_E = 1.0 Vdc)	2N3904 2N3903		100 30	300	
(I _C = 100 mAdc, V ₀		2N3904 2N3903		60 15		
(10 - 100 11) (40, 7)	GE = 1.0 Va0)	2N3904		30	_	
Collector – Emitter ($I_C = 10 \text{ mAdc}$, $I_B = I_C = I_C$			V _{CE(sat)}	_ _	0.2 0.3	Vdc
Base – Emitter Sati (I _C = 10 mAdc, I _B = (I _C = 50 mAdc, I _B =		V _{BE(sat)}	0.65	0.85 0.95	Vdc	
•	CHARACTERISTICS			<u> </u>		
Current – Gain – Ba (I _C = 10 mAdc, V _C	andwidth Product E = 20 Vdc, f = 100 MHz)	2N3903 2N3904	f _T	250 300	- -	MHz
Output Capacitano	ce (V _{CB} = 5.0 Vdc, I _E = 0, f = 1.0 MHz)		C _{obo}	_	4.0	pF
Input Capacitance	(V _{EB} = 0.5 Vdc, I _C = 0, f = 1.0 MHz)		C _{ibo}	_	8.0	pF
Input Impedance	_{DE} = 10 Vdc, f = 1.0 kHz)	2N3903 2N3904	h _{ie}	1.0 1.0	8.0 10	kΩ
Voltage Feedback (I _C = 1.0 mAdc, V _C	Ratio _{CE} = 10 Vdc, f = 1.0 kHz)	2N3903 2N3904	h _{re}	0.1 0.5	5.0 8.0	X 10 ⁻⁴
Small-Signal Curro (I _C = 1.0 mAdc, V _C	2N3903 2N3904	h _{fe}	50 100	200 400	-	
Output Admittance		h _{oe}	1.0	40	μmhos	
Noise Figure (I _C = 100 μAdc, V _C	NF	- -	6.0 5.0	dB		
SWITCHING CHA	RACTERISTICS					•
Delay Time	(V _{CC} = 3.0 Vdc, V _{BE} = 0.5 Vdc,		t _d	-	35	ns
Rise Time	I _C = 10 mAdc, I _{B1} = 1.0 mAdc)		t _r	-	35	ns
Storage Time	$(V_{CC} = 3.0 \text{ Vdc}, I_C = 10 \text{ mAdc}, I_{B1} = I_{B2} = 1.0 \text{ mAdc})$	2N3903 2N3904	t _s	- -	175 200	ns
Fall Time			t _f	_	50	ns

^{2.} Pulse Test: Pulse Width ≤ 300 μs; Duty Cycle ≤ 2%.

ORDERING INFORMATION

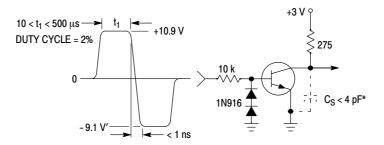
Device	Package	Shipping [†]
2N3903RLRM	TO-92	2000 / Ammo Pack
2N3904	TO-92	5000 Units / Bulk
2N3904G	TO-92 (Pb-Free)	5000 Units / Bulk
2N3904RLRA	TO-92	2000 / Tape & Reel
2N3904RLRAG	TO-92 (Pb-Free)	2000 / Tape & Reel
2N3904RLRM	TO-92	2000 / Ammo Pack
2N3904RLRMG	TO-92 (Pb-Free)	2000 / Ammo Pack
2N3904RLRP	TO-92	2000 / Ammo Pack
2N3904RLRPG	TO-92 (Pb-Free)	2000 / Ammo Pack
2N3904RL1G	TO-92 (Pb-Free)	2000 / Tape & Reel
2N3904ZL1	TO-92	2000 / Ammo Pack
2N3904ZL1G	TO-92 (Pb-Free)	2000 / Ammo Pack

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



^{*} Total shunt capacitance of test jig and connectors

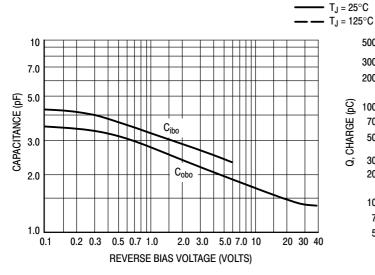
Figure 1. Delay and Rise Time Equivalent Test Circuit



^{*} Total shunt capacitance of test jig and connectors

Figure 2. Storage and Fall Time Equivalent Test Circuit

TYPICAL TRANSIENT CHARACTERISTICS



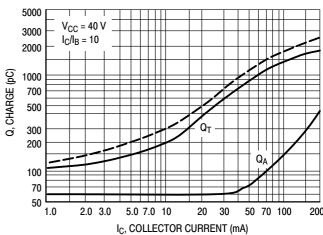
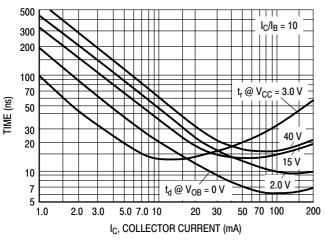


Figure 3. Capacitance

Figure 4. Charge Data



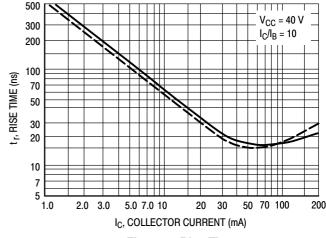
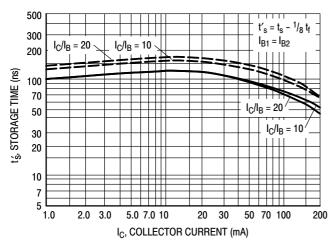


Figure 5. Turn-On Time

Figure 6. Rise Time



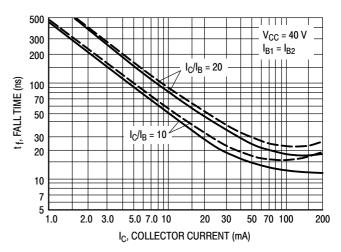
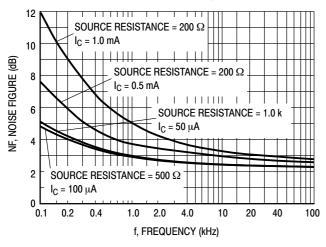


Figure 7. Storage Time

Figure 8. Fall Time

TYPICAL AUDIO SMALL-SIGNAL CHARACTERISTICS NOISE FIGURE VARIATIONS

 $(V_{CE} = 5.0 \text{ Vdc}, T_A = 25^{\circ}\text{C}, Bandwidth = 1.0 \text{ Hz})$



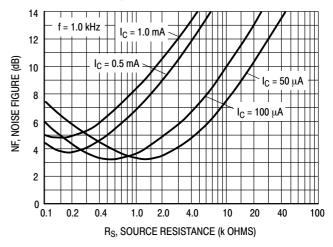
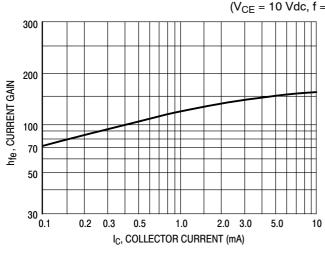


Figure 9.

Figure 10.

h PARAMETERS



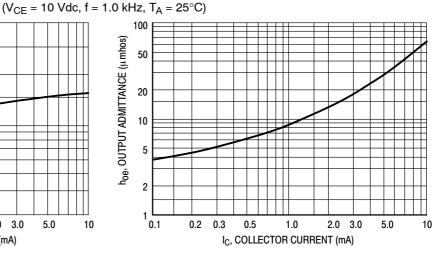


Figure 11. Current Gain

Figure 12. Output Admittance

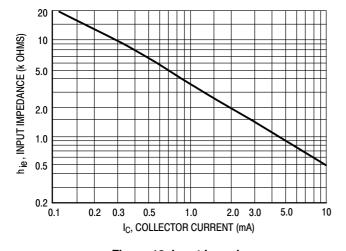




Figure 13. Input Impedance

Figure 14. Voltage Feedback Ratio

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TYPICAL STATIC CHARACTERISTICS

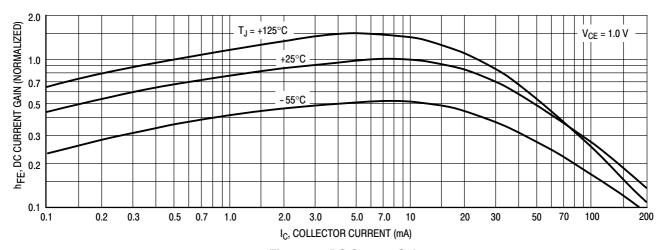


Figure 15. DC Current Gain

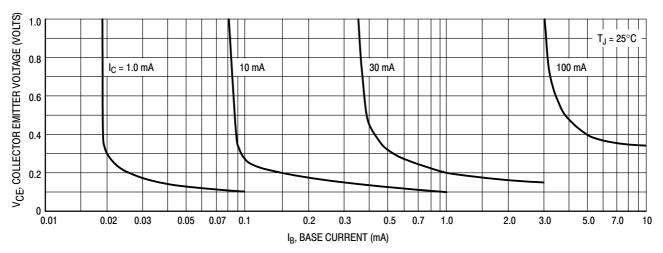


Figure 16. Collector Saturation Region

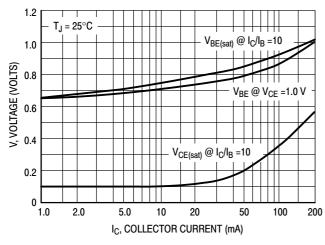


Figure 17. "ON" Voltages

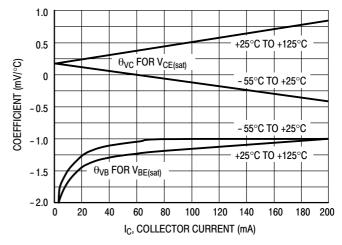
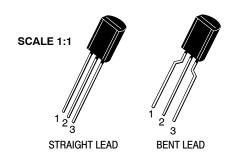
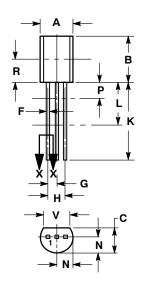


Figure 18. Temperature Coefficients



TO-92 (TO-226) 1 WATT CASE 29-10 **ISSUE A**

DATE 08 MAY 2012



STRAIGHT LEAD







NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI
- 714.5M, 1994.
 CONTROLLING DIMENSION: INCHES.
 CONTOUR OF PACKAGE BEYOND DIMENSION R IS
 UNCONTROLLED.
- UNIONI HOLLEU, DIMENSION F APPLIES BETWEEN DIMENSIONS P AND L DIMENSIONS D AND J APPLY BETWEEN DI-MENSIONS L AND K MINIMUM. THE LEAD DIMENSIONS ARE UNCONTROLLED IN DIMENSION P AND BEYOND DIMENSION K MINIMUM.

	INC	HES	MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.44	5.21
В	0.290	0.310	7.37	7.87
С	0.125	0.165	3.18	4.19
D	0.018	0.021	0.46	0.53
F	0.016	0.019	0.41	0.48
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.018	0.024	0.46	0.61
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
Р		0.100		2.54
R	0.135		3.43	
٧	0.135		3.43	

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME
- CONTROLLING DIMENSION: INCHES.
 CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
- DIMENSION F APPLIES BETWEEN DIMENSIONS P AND L. DIMENSIONS D AND J APPLY BETWEEN DIMENSIONS L AND K MINIMUM. THE LEAD DIMENSIONS ARE UNCONTROLLED IN DIMENSION P AND BEYOND DIMENSION K MINIMUM.

	INC	HES	MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.44	5.21
В	0.290	0.310	7.37	7.87
С	0.125	0.165	3.18	4.19
D	0.018	0.021	0.46	0.53
G	0.094	0.102	2.40	2.80
J	0.018	0.024	0.46	0.61
K	0.500		12.70	
N	0.080	0.105	2.04	2.66
P		0.100		2.54
R	0.135		3.43	
٧	0.135		3.43	

STYLES ON PAGE 2

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SEATING PLANE

TO-92 (TO-226) 1 WATT CASE 29-10

ISSUE A

DATE 08 MAY 2012

STYLE 1: PIN 1. 2. 3.	EMITTER BASE COLLECTOR	STYLE 2: PIN 1. 2. 3.	BASE EMITTER COLLECTOR	STYLE 3: PIN 1. 2. 3.	ANODE ANODE CATHODE	STYLE 4: PIN 1. 2. 3.	CATHODE CATHODE ANODE	STYLE 5: PIN 1. 2. 3.	DRAIN SOURCE GATE
STYLE 6: PIN 1. 2. 3.	GATE SOURCE & SUBSTRATE DRAIN	STYLE 7: PIN 1. 2. 3.	SOURCE DRAIN GATE	STYLE 8: PIN 1. 2. 3.	DRAIN GATE SOURCE & SUBSTRATE	STYLE 9: PIN 1. 2. 3.	BASE 1 EMITTER BASE 2	STYLE 10: PIN 1. 2. 3.	
2. 3.	CATHODE & ANODE CATHODE	2. 3.	GATE MAIN TERMINAL 2	2. 3.		2. 3.	COLLECTOR BASE	2. 3.	CATHODE ANODE 2
STYLE 16: PIN 1. 2. 3.	ANODE GATE CATHODE	STYLE 17: PIN 1. 2. 3.	COLLECTOR BASE EMITTER	STYLE 18: PIN 1. 2. 3.	ANODE CATHODE NOT CONNECTED	STYLE 19: PIN 1. 2. 3.	GATE ANODE CATHODE	STYLE 20: PIN 1. 2. 3.	NOT CONNECTED CATHODE ANODE
PIN 1. 2.	COLLECTOR EMITTER	PIN 1.		PIN 1. 2.	GATE SOURCE DRAIN	PIN 1. 2.	EMITTER COLLECTOR/ANODE CATHODE	PIN 1. 2.	MT 1
3.	V _{CC} GROUND 2 OUTPUT	PIN 1. 2. 3.	MT SUBSTRATE MT	PIN 1. 2. 3.	ANODE GATE	PIN 1. 2. 3.	NOT CONNECTED ANODE CATHODE	PIN 1. 2.	DRAIN
2.	GATE DRAIN SOURCE	2.	BASE COLLECTOR EMITTER	2.	RETURN INPUT OUTPUT	2.	INPUT GROUND LOGIC		GATE COLLECTOR EMITTER

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